

60V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary NPN Type: MMBT2222A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

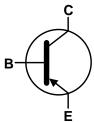
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

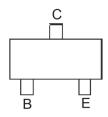




Top View



Device Symbol



Top View Pin-Out

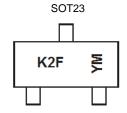
Ordering Information (Notes 4 & 5)

| Product | Status | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|--------|------------|---------|--------------------|-----------------|-------------------|
| MMBT2907A-7-F | NRND | AEC-Q101 | K2F | 7 | 8 | 3,000 |
| MMBT2907A-7 | Active | AEC-Q101 | K2F | 7 | 8 | 3,000 |
| MMBT2907A-13-F | NRND | AEC-Q101 | K2F | 13 | 8 | 10,000 |
| MMBT2907A-13 | Active | AEC-Q101 | K2F | 13 | 8 | 10,000 |
| MMBT2907AQ-7-F | Active | Automotive | K2F | 7 | 8 | 3,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. NRND = Not Recommended for New Design. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K2F = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: A = 2013) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2013 | | 2014 | 2015 | | 2016 | 2017 | | 2018 | 2019 | | 2020 |
|-------|------|-----|------|------|-----|------|------|-----|------|------|-----|------|
| Code | Α | | В | С | | D | E | | F | G | | Н |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | -60 | V |
| Collector-Emitter Voltage | V _{CEO} | -60 | V |
| Emitter-Base Voltage | V_{EBO} | -6.0 | V |
| Collector Current | lc | -600 | mA |
| Peak Collector Current | I _{CM} | -800 | mA |
| Peak Base Current | Івм | -200 | mA |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit | |
|--|---------------------|-------------------|-------|------|--|
| Collector Power Dissipation | (Note 6) | D- | 310 | mW | |
| Collector Fower Dissipation | (Note 7) | P _D | 350 | | |
| Thermal Resistance, Junction to Ambient | (Note 6) | D | 403 | °C/W | |
| Thermal Resistance, Junction to Ambient | (Note 7) | R ₀ JA | 357 | | |
| Thermal Resistance, Junction to Leads (Note 8) | | $R_{	heta JL}$ | 350 | °C/W | |
| Operating and Storage Temperature Range | T_{J} , T_{STG} | -55 to +150 | °C | | |

ESD Ratings (Note 9)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

Notes:

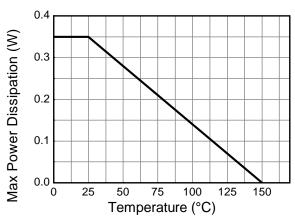
^{6.} For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

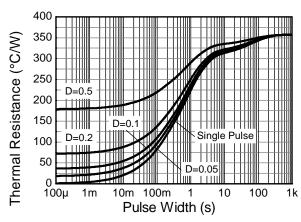
^{7.} Same as Note 6, except the device is mounted on 15 mm x 15mm 1oz copper.

^{8.} Thermal resistance from junction to solder-point (at the end of the leads). 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



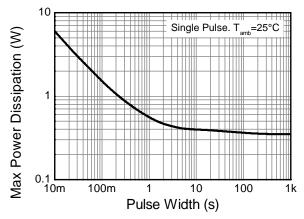
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Max | Unit | Test Condition |
|---|----------------------|-------------------------------|-----------------|----------|---|
| OFF CHARACTERISTICS | | | | | |
| Collector-Base Breakdown Voltage | BV _{CBO} | -60 | _ | V | $I_C = -100\mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage (Note 10) | BV _{CEO} | -60 | _ | V | $I_C = -10 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -6.0 | _ | V | $I_E = -100 \mu A, I_C = 0$ |
| Collector Cut-Off Current | I _{CBO} | _ | -10 | nΑ μΑ | $V_{CB} = -50V, I_E = 0$ $V_{CB} = -50V, I_E = 0, T_A = +125$ °C |
| Collector Cut-Off Current | I _{CEX} | _ | -50 | nA | $V_{CE} = -30V, V_{EB(OFF)} = -0.5V$ |
| Base Cut-Off Current | I _{BL} | _ | -50 | nA | $V_{CE} = -30V, V_{EB(OFF)} = -0.5V$ |
| Emitter Cut-Off Current | I _{EBO} | _ | -50 | nA | V _{EB} = -6.0V |
| ON CHARACTERISTICS (Note 10) | | • | | | |
| DC Current Gain | h _{FE} | 75 100 100 100 50 | 300 | | $I_C = -100\mu A, V_{CE} = -10V$ $I_C = -1.0mA, V_{CE} = -10V$ $I_C = -10mA, V_{CE} = -10V$ $I_C = -150mA, V_{CE} = -10V$ $I_C = -500mA, V_{CE} = -10V$ |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | _ | -0.4 -1.6 | V | $I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$ |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | _ | -1.3 -2.6 | ٧ | I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA |
| SMALL SIGNAL CHARACTERISTICS | • | | | | , - |
| Output Capacitance | C _{obo} | _ | 8.0 | pF | $V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$ |
| Input Capacitance | C _{ibo} | _ | 30 | pF | $V_{EB} = -2.0V$, $f = 1.0MHz$, $I_{C} = 0$ |
| Current Gain-Bandwidth Product | f⊤ | 200 | _ | MHz | $V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz |
| SWITCHING CHARACTERISTICS | | | | | |
| Turn-On Time | t _{off} | _ | 45 | ns | $V_{CC} = -30V, I_{C} = -150mA,$ |
| Delay Time | t _d | _ | 10 | ns | $V_{CC} = -30V, I_{C} = -150MA,$ $I_{B1} = -15MA$ |
| Rise Time | t _r | _ | 40 | ns | IBI — FISHIM |
| Turn-Off Time | t _{off} | _ | 100 | ns | V _{CC} = -6.0V, I _C = -150mA, |
| Storage Time | ts | _ | 80 | ns | $V_{CC} = -6.0V, I_{C} = -150\text{mA},$ $I_{B1} = I_{B2} = -15\text{mA}$ |
| Fall Time | t _f | _ | 30 | ns | 101 - 102 - 101117 |

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



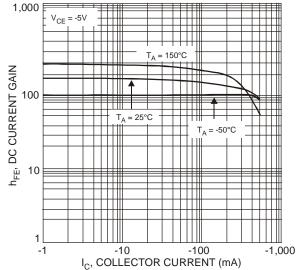


Fig. 1 Typical DC Current Gain vs. Collector Current

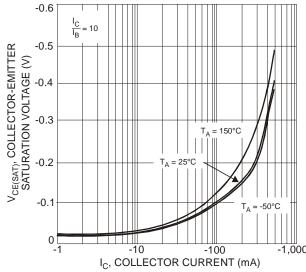


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

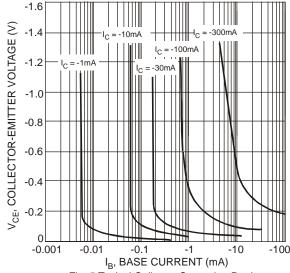


Fig. 5 Typical Collector Saturation Region

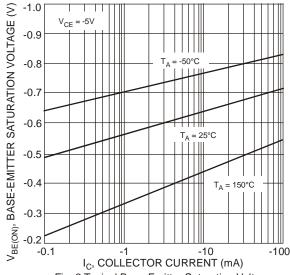


Fig. 2 Typical Base-Emitter Saturation Voltage vs. Collector Current

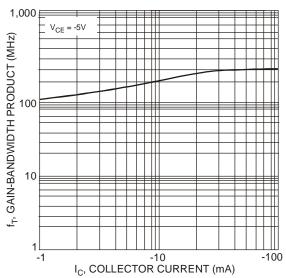


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current

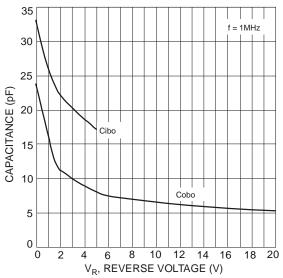
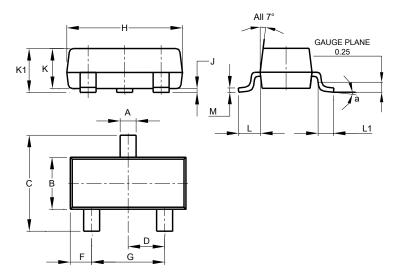


Fig. 6 Typical Capacitance Characteristics



Package Outline Dimensions

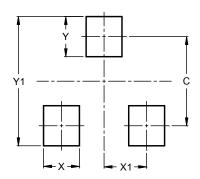
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| SOT23 | | | | | | | |
|-------|----------------------|-------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | | |
| В | 1.20 | 1.40 | 1.30 | | | | |
| С | 2.30 | 2.50 | 2.40 | | | | |
| D | 0.89 | 1.03 | 0.915 | | | | |
| F | 0.45 | 0.60 | 0.535 | | | | |
| G | 1.78 | 2.05 | 1.83 | | | | |
| Н | 2.80 | 3.00 | 2.90 | | | | |
| J | 0.013 | 0.10 | 0.05 | | | | |
| K | 0.890 | 1.00 | 0.975 | | | | |
| K1 | 0.903 | 1.10 | 1.025 | | | | |
| L | 0.45 | 0.61 | 0.55 | | | | |
| L1 | 0.25 | 0.55 | 0.40 | | | | |
| М | 0.085 | 0.150 | 0.110 | | | | |
| а | 0° | 8° | | | | | |
| All | All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.0 |
| Х | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 29 |



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